

Dinh Loc Duong

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4367919/publications.pdf>

Version: 2024-02-01

64
papers

4,525
citations

147801
31
h-index

102487
66
g-index

69
all docs

69
docs citations

69
times ranked

8369
citing authors

#	ARTICLE	IF	CITATIONS
1	van der Waals Layered Materials: Opportunities and Challenges. <i>ACS Nano</i> , 2017, 11, 11803-11830.	14.6	394
2	Probing graphene grain boundaries with optical microscopy. <i>Nature</i> , 2012, 490, 235-239.	27.8	352
3	Confocal absorption spectral imaging of MoS ₂ : optical transitions depending on the atomic thickness of intrinsic and chemically doped MoS ₂ . <i>Nanoscale</i> , 2014, 6, 13028-13035.	5.6	319
4	Seamless Stitching of Graphene Domains on Polished Copper (111) Foil. <i>Advanced Materials</i> , 2015, 27, 1376-1382.	21.0	314
5	Transferred wrinkled Al ₂ O ₃ for highly stretchable and transparent graphene "carbon nanotube" transistors. <i>Nature Materials</i> , 2013, 12, 403-409.	27.5	295
6	van der Waals Metallic Transition Metal Dichalcogenides. <i>Chemical Reviews</i> , 2018, 118, 6297-6336.	47.7	252
7	Reduction-Controlled Viologen in Bisolvent as an Environmentally Stable n-Type Dopant for Carbon Nanotubes. <i>Journal of the American Chemical Society</i> , 2009, 131, 327-331.	13.7	196
8	Charge Transport in Polycrystalline Graphene: Challenges and Opportunities. <i>Advanced Materials</i> , 2014, 26, 5079-5094.	21.0	166
9	Role of Anions in the AuCl ₃ -Doping of Carbon Nanotubes. <i>ACS Nano</i> , 2011, 5, 1236-1242.	14.6	149
10	Ferromagnetic Order at Room Temperature in Monolayer WSe ₂ Semiconductor via Vanadium Dopant. <i>Advanced Science</i> , 2020, 7, 1903076.	11.2	148
11	Ultra-transparent, Flexible Single-walled Carbon Nanotube Non-volatile Memory Device with an Oxygen-decorated Graphene Electrode. <i>Advanced Materials</i> , 2011, 23, 1889-1893.	21.0	118
12	Alumina-coated silicon-based nanowire arrays for high quality Li-ion battery anodes. <i>Journal of Materials Chemistry</i> , 2012, 22, 24618.	6.7	116
13	Facile Physical Route to Highly Crystalline Graphene. <i>Advanced Functional Materials</i> , 2011, 21, 3496-3501.	14.9	97
14	Stranski-Krastanov and Volmer-Weber CVD Growth Regimes To Control the Stacking Order in Bilayer Graphene. <i>Nano Letters</i> , 2016, 16, 6403-6410.	9.1	95
15	Telluriding monolayer MoS ₂ and WS ₂ via alkali metal scooter. <i>Nature Communications</i> , 2017, 8, 2163.	12.8	87
16	Negative and Positive Persistent Photoconductance in Graphene. <i>Nano Letters</i> , 2011, 11, 4682-4687.	9.1	82
17	Transfer-free Growth of Few-layer Graphene by Self-assembled Monolayers. <i>Advanced Materials</i> , 2011, 23, 4392-4397.	21.0	79
18	Layer-controlled single-crystalline graphene film with stacking order via Cu-Si alloy formation. <i>Nature Nanotechnology</i> , 2020, 15, 861-867.	31.5	79

#	ARTICLE	IF	CITATIONS
19	Improving the wettability of aluminum on carbon nanotubes. <i>Acta Materialia</i> , 2011, 59, 3313-3320.	7.9	66
20	Monodispersed SnS nanoparticles anchored on carbon nanotubes for high-retention sodium-ion batteries. <i>Journal of Materials Chemistry A</i> , 2020, 8, 7861-7869.	10.3	60
21	Raman Characterization of the Charge Density Wave Phase of 1T-TiSe ₂ : From Bulk to Atomically Thin Layers. <i>ACS Nano</i> , 2017, 11, 1034-1040.	14.6	58
22	Transparent Organic P-Dopant in Carbon Nanotubes: Bis(trifluoromethanesulfonyl)imide. <i>ACS Nano</i> , 2010, 4, 6998-7004.	14.6	56
23	Chemically Modulated Band Gap in Bilayer Graphene Memory Transistors with High On/Off Ratio. <i>ACS Nano</i> , 2015, 9, 9034-9042.	14.6	56
24	Thin-layer black phosphorus/GaAs heterojunction p-n diodes. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	55
25	Humidity-assisted selective reactivity between NO ₂ and SO ₂ gas on carbon nanotubes. <i>Journal of Materials Chemistry</i> , 2011, 21, 4502.	6.7	54
26	Ultrahigh Gauge Factor in Graphene/MoS ₂ Heterojunction Field Effect Transistor with Variable Schottky Barrier. <i>ACS Nano</i> , 2019, 13, 8392-8400.	14.6	54
27	Direct growth of etch pit-free GaN crystals on few-layer graphene. <i>RSC Advances</i> , 2015, 5, 1343-1349.	3.6	46
28	Nondestructive Characterization of Graphene Defects. <i>Advanced Functional Materials</i> , 2013, 23, 5183-5189.	14.9	44
29	TiS_{2} 3.2 Physical Review B, 2015, 92, .	44	
30	Role of Hole Trap Sites in MoS ₂ for Inconsistency in Optical and Electrical Phenomena. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 10580-10586.	8.0	37
31	UV-LIGHT-ASSISTED OXIDATIVE sp ³ HYBRIDIZATION OF GRAPHENE. <i>Nano</i> , 2011, 06, 409-418.	1.0	36
32	Hygroscopic Effects on AuCl ₃ -Doped Carbon Nanotubes. <i>Journal of Physical Chemistry C</i> , 2010, 114, 11618-11622.	3.1	33
33	Carbon Nanotube Doping Mechanism in a Salt Solution and Hygroscopic Effect: Density Functional Theory. <i>ACS Nano</i> , 2010, 4, 5430-5436.	14.6	32
34	Long-range ferromagnetic ordering in vanadium-doped WSe ₂ semiconductor. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	31
35	Band-gap engineering in chemically conjugated bilayer graphene: <i>Ab initio</i> calculations. <i>Physical Review B</i> , 2012, 85, .	3.2	29
36	Probing Multiphased Transition in Bulk MoS ₂ by Direct Electron Injection. <i>ACS Nano</i> , 2019, 13, 14437-14446.	14.6	29

#	ARTICLE	IF	CITATIONS
37	Efficient Photothermoelectric Conversion in Lateral Topological Insulator Heterojunctions. <i>Nano Letters</i> , 2017, 17, 214-219.	9.1	28
38	High Performance Grapheneâ€“Oxideâ€“Metal Diode through Biasâ€“Induced Barrier Height Modulation. <i>Advanced Electronic Materials</i> , 2016, 2, 1600223.	5.1	25
39	Ultrashort Verticalâ€“Channel van der Waals Semiconductor Transistors. <i>Advanced Science</i> , 2020, 7, 1902964.	11.2	24
40	Electrically tunable quantum emitters in an ultrathin grapheneâ€“hexagonal boron nitride van der Waals heterostructure. <i>Applied Physics Letters</i> , 2019, 114, .	3.3	23
41	Breaking AB stacking order in graphite oxide: ab initio approach. <i>Physical Chemistry Chemical Physics</i> , 2010, 12, 1595.	2.8	21
42	Escalating Ferromagnetic Order via Seâ€“Vacancies Near Vanadium in WSe ₂ Monolayers. <i>Advanced Materials</i> , 2022, 34, e2106551.	21.0	20
43	Spectroscopic Determination of the Electrochemical Potentials of n-Type Doped Carbon Nanotubes. <i>Journal of Physical Chemistry C</i> , 2012, 116, 5444-5449.	3.1	17
44	Lightâ€“Controlled Room Temperature Ferromagnetism in Vanadiumâ€“Doped Tungsten Disulfide Semiconducting Monolayers. <i>Advanced Electronic Materials</i> , 2021, 7, 2100030.	5.1	17
45	Doping-Mediated Lattice Engineering of Monolayer ReS ₂ for Modulating In-Plane Anisotropy of Optical and Transport Properties. <i>ACS Nano</i> , 2021, 15, 13770-13780.	14.6	17
46	Revealing antiferromagnetic transition of van der Waals MnPS ₃ via vertical tunneling electrical resistance measurement. <i>APL Materials</i> , 2019, 7, .	5.1	16
47	Evidence of itinerant holes for long-range magnetic order in the tungsten diselenide semiconductor with vanadium dopants. <i>Physical Review B</i> , 2021, 103, .	3.2	16
48	Hot Carrier Extraction from Multilayer Graphene. <i>Nano Letters</i> , 2016, 16, 6761-6766.	9.1	15
49	Origin of unipolarity in carbon nanotube field effect transistors. <i>Journal of Materials Chemistry</i> , 2012, 22, 1994-1997.	6.7	14
50	Graphene/ferroelectrics/graphene hybrid structure: Asymmetric doping of graphene layers. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	13
51	Spin-Selective Holeâ€“Exciton Coupling in a V-Doped WSe ₂ Ferromagnetic Semiconductor at Room Temperature. <i>ACS Nano</i> , 2021, 15, 20267-20277.	14.6	13
52	Gate modulation of the long-range magnetic order in a vanadium-doped WSe ₂ semiconductor. <i>AIP Advances</i> , 2020, 10, .	1.3	12
53	Probing giant Zeeman shift in vanadium-doped $\text{W}_{\text{2-x}}\text{Se}_{\text{x}}$ via resonant magnetotunneling transport. <i>Physical Review B</i> , 2021, 103, .	3.2	12
54	Light-emitting Ti ₂ N (MXene) quantum dots: synthesis, characterization and theoretical calculations. <i>Journal of Materials Chemistry C</i> , 2022, 10, 6508-6514.	5.5	10

#	ARTICLE	IF	CITATIONS
55	Proximity Engineering of the van der Waals Interaction in Multilayered Graphene. ACS Applied Materials & Interfaces, 2019, 11, 42528-42533.	8.0	9
56	Li Intercalation Effects on Interface Resistances of High-Speed and Low-Power WSe ₂ Field-Effect Transistors. Advanced Functional Materials, 2020, 30, 2003688.	14.9	9
57	Carrier transport mechanisms of reactively direct current magnetron sputtered tungsten oxide/n-type crystalline silicon heterojunction. Journal of Power Sources, 2020, 472, 228460.	7.8	5
58	Gate-Tunable Magnetism via Resonant Se-Vacancy Levels in WSe ₂ . Advanced Science, 2021, , 2102911.	11.2	5
59	Defect-Engineered Magnetic Field Dependent Optoelectronics of Vanadium Doped Tungsten Diselenide Monolayers. Advanced Optical Materials, 0, , 2102711.	7.3	5
60	Schottky-barrier quantum well in two-dimensional semiconductor nanotransistors. Materials Today Physics, 2020, 15, 100275.	6.0	4
61	Oxidize Graphene by UV-Ozone Treatment in Vacuum Chamber. Journal of Nanoscience and Nanotechnology, 2016, 16, 7968-7972.	0.9	2
62	Different mechanism of capacitance change for gas detection using semiconducting and metallic single-walled carbon nanotubes. Current Applied Physics, 2015, 15, 377-382.	2.4	1
63	V ₂ Se: a novel antifluorite-type cubic phase with a metal-metal bonding. Dalton Transactions, 2019, 48, 8556-8559.	3.3	1
64	Tuning the inhomogeneous charge transport in ZnO interfaces for ultrahigh on/off ratio top-gated field-effect-transistor arrays. Nano Research, 2020, 13, 3033-3040.	10.4	1